imall

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High Voltage LED Series Chip on Board

LCO40B



High efficacy COB LED package, well-suited for use in spotlight applications

Features & Benefits

- Chip on Board (COB) solution makes it easy to design in
- Simple assembly reduces manufacturing cost
- Low thermal resistance
- InGaN/GaN MQW LED with long time reliability
- Completed 6,000 hours of LM-80 Testing

Applications

- Spotlight / Downlight
- LED Retrofit Bulbs
- Outdoor Illumination



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1. Characteristics

a) Absolute Maximum Rating

ltem	Symbol	Rating	Unit	Condition
Ambient / Operating Temperature	T _a	-40 ~ +105	Co	-
Storage Temperature	T _{stg}	-40 ~ +120	°C	_
LED Junction Temperature	Tj	150	°C	-
Case Temperature	Tc	105	°C	*Note
Forward Current	lF	1900	mA	_
Power Dissipation	PD	70.3	W	-
ESD (HBM)	-	±2	kV	-
ESD (MM)	_	±0.5	kV	-

b) Electro-optical Characteristics (I_F = 1080 mA, T_c = 25 °C)

ltem	Unit	Rank	Min.	Тур.	Max.
Forward Voltage (V _F)	V	YH	32.5	35.5	38.5
		3	70	-	-
Color Dondoring Index (D)		5	80 (R9 > 0)	-	-
Color Rendering Index (Ra)	-	7	90	-	-
		8	95		
Thermal Resistance (junction to chip point)	°C/W		-	0.8	-
Beam Angle	0		-	115	-
Working Voltage for Insulation	V				50
Nominal Power	W			38.3	

Notes:

- 1) The COB is tested in pulsed condition at rated test current (10 ms pulse width) and rated temperature ($T_j = T_c = T_a = 25$ °C)
- 2) Samsung maintains measurement tolerance of: forward voltage = ± 5 %, CRI = ± 1
- 3) Refer to the derating curve, '3. Typical Characteristics Graph' designed within the range.



c) Luminous Flux Characteristics (I_F = 1080 mA)

CRI (R _a)	Nominal	Flux	Flux	Sorting ¹⁾ @	T _c = 25 °C (lm)	Calculated Flux ²⁾ @ T _c	= 85 °C (In
Min.	CCT (K)	Rank	Bin	Min.	Max.	Min.	Max.
	3000	4J	41	4776	5428	4299	4885
	3000	4J	42	5428	6079	4885	5471
70	4000	4J	41	5063	5753	4557	5178
70	4000	40	42	5753	6444	5178	5799
	5000	C 1	51	5111	5808	4600	5227
	5000	5J	52	5808	6505	5227	5854
			42	4050	4400	3686	4004
		4.1	43	4400	4750	4004	4323
	0700	4J	44	4750	5100	4323	4641
	2700		45	5100	5450	4641	4960
		40	44	4750	5100	4323	4641
		4G	45	5100	5450	4641	4960
			42	4175	4535	3799	4127
			43	4535	4895	4127	4454
		4J	44	4895	5255	4454	4782
	3000		45	5255	5615	4782	5110
			44	4895	5255	4454	4782
		4G	45	5255	5615	4782	5110
			42	4340	4720	3949	4295
	3500		43	4720	5100	4295	4641
		4J	44	5100	5480	4641	4987
			45	5480	5860	4987	5333
			44	5100	5480	4641	4987
		4G	45	5480	5860	4987	5333
80			42	4465	4855	4063	4418
			43	4855	5245	4418	4773
		4J	44	5245	5635	4773	5128
	4000		45	5635	6025	5128	5483
			44	5245	5635	4773	5128
		4G	45	5635	6025	5128	5483
			42	4505	4900	4100	4459
			43	4900	5295	4459	4818
		4J	44	5295	5690	4818	5178
	5000		45	5690	6085	5178	5537
			44	5295	5690	4818	5178
		4G	45	5690	6085	5178	5537
			42	4505	4900	4100	4459
			43	4900	5295	4459	4818
		4J	44	5295	5690	4818	5178
	5700		45	5690	6085	5178	5537
			44	5295	5690	4818	5178
		4G	44	5690	6085	5178	5537



c) Luminous Flux Characteristics ($I_F = 1080 \text{ mA}$)

CRI (R _a)	Nominal	Flux	Flux	Sorting ¹⁾ @T	_c = 25 °C (lm)	Calculated Flux ²⁾	@ T _c = 85 °C (Im)
Min.	CCT (K)	Rank	Bin	Min.	Max.	Min.	Max.
			42	3465	3795	3154	3454
	2700	4J	43	3795	4126	3454	3754
			44	4126	4456	3754	4055
			42	3536	3873	3218	3524
	3000	4J	43	3873	4210	3524	3831
00			44	4210	4546	3831	4137
90	3500		42	3642	3989	3314	3630
		4J	43	3989	4336	3630	3946
			44	4336	4683	3946	4261
		4J	42	3748	4105	3411	3736
	4000		43	4105	4462	3736	4061
			44	4462	4819	4061	4386
	2700	3M	31	3394	3771	3088	3432
	2700	31VI	32	3771	4148	3432	3775
95	2000	3M	31	3499	3888	3184	3538
	3000	3171	32	3888	4276	3538	3892
	2500	3M	31	3604	4004	3280	3644
	3500	SIVI	32	4004	4405	3644	4008

Notes:

- 1) The COB is tested in pulsed condition at rated test current (10 ms pulse width) and rated temperature ($T_j = T_c = T_a = 25$ °C)
- 2) Calculated flux values are for reference only
- 3) Samsung maintains measurement tolerance of: Iuminous flux = ± 7 %, CRI = ± 1



2. Product Code Information

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
S																	

Digit	PKG Information	Code				Specificat	ion
1 2 3	Samsung Package High Power	SPH					
4.5	Ostar	ww	Warm White	(T/U/	V/W Rank	s)	
4 5	Color	cw	Cool White	(Q/R	Ranks)		
6	Product Version	1					
78	Form Factor	HD	СОВ				
9	Lens Type	N	No lens				
10	Internal Code	Е	LC040				
11	Chip Type	2					
		3	Min. 70				
12	CRI & Sorting Temperature	5	Min. 80	°C			
12	Chi & Solung Temperature	7	Min. 90	0			
		8	Min 95				
13 14	Forward Voltage (V)	YH	32.5~38.5				
		w	2700 K		WA,WB	(MacAdam Ellipse)	
		v	3000 K		VA, VB	(MacAdam Ellipse)	VW, VX, VY, VZ (ANSI bin)
15	CCT (K)	U		Bin	UA, UB	(MacAdam Ellipse)	
15	001 (K)	т	4000 K ^{Co}	ode:	TA, TB	(MacAdam Ellipse)	TW, TX, TY, TZ (ANSI bin)
		R	5000 K		RA	(MacAdam Ellipse)	RW, RX, RY, RZ (ANSI bin)
		Q	5700 K				QW, QX, QY, QZ (ANSI bin)
		2	MacAdam 2-s	step			
16	MacAdam / ANSI	3	MacAdam 3-s	step			
		т	ANSI bin				
		3M			31, 32 (95	5 CRI)	
17 18	Luminous Flux	4J		Bin	42, 43, 44	(90 CRI); 42, 43, 44, 45	(80 CRI); 41, 42 (70 CRI)
17 10	Luminous Hux	4G	Co	ode:	44, 45 (8	30 CRI)	
		5J			51,52 (7	70 CRI)	





a) Binning Structure (IF = 1080 mA, Tc = 25 °C)

CRI (R₄) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)	
	3000	SPHWW1HDNE23YHVT4J	ΥH	VT	VW, VX	4J	41	4776 ~ 5428	
	3000	SERVIV INDIVEZSI NV145		VI	VY, VZ	4J	42	5428 ~ 6079	
70	4000	SPHWW1HDNE23YHTT4J	ΥH	Π	TW, TX	4J	41	5063 ~ 5753	
10	4000	SFTWWWITIDINE2STTTT40			TY, TZ	40	42	5753 ~ 6444	
	5000	SPHCW1HDNE23YHRT5J	ΥH	RT	RW, RX	5J	51	5111 ~ 5808	
	5000	SETIOWTHDNE25THITIS		111	RY, RZ	50	52	5808 ~ 6505	
							42	4050 ~ 4400	
		SPHWW1HDNE25YHW24J	ΥH	W2	WB	4J	43	4400 ~ 4750	
		OF THE WITH DIVEZOFTINZ TO		VVZ	VVD	40	44	4750 ~ 5100	
							45	5100 ~ 5450	
							42	4050 ~ 4400	
	2700	2700	SPHWW1HDNE25YHW34J	ΥH	W3	WA, WB	4J	43	4400 ~ 4750
		3F11000011DNL2311100343		VV3	WA, WD	40	44	4750 ~ 5100	
							45	5100 ~ 5450	
		SPHWW1HDNE25YHW24G	ΥH	W2	WB	4G	44	4750 ~ 5100	
		SFTWWTHDNE23TTW24G		VVZ	VVD	40	45	5100 ~ 5450	
		SPHWW1HDNE25YHW34G	ΥH	W3	WA, WB	4G	44	4750 ~ 5100	
80		SFTWWTHDNE25TTW34G	111	VV3	VVA, VVD	40	45	5100 ~ 5450	
00							42	4175 ~ 4535	
		SPHWW1HDNE25YHV24J	ΥH	V2	VB	4J	43	4535 ~ 4895	
		SPRWWINDNez5TRV24J	ΤΠ	٧Z	VD	40	44	4895 ~ 5255	
							45	5255 ~ 5615	
							42	4175 ~ 4535	
	3000	SPHWW1HDNE25YHV34J	ΥH	V3		41	43	4535 ~ 4895	
	3000			vo	VA, VB	4J	44	4895 ~ 5255	
							45	5255 ~ 5615	
		SPHWW1HDNE25YHV24G	ΥH	V2	VB	4G	44	4895 ~ 5255	
		SPRIVIN INDINE231 HV24G	τΗ	٧Z	٧B	40	45	5255 ~ 5615	
			VL	1/2		40	44	4895 ~ 5255	
		SPHWW1HDNE25YHV34G	ΥH	V3	VA, VB	4G	45	5255 ~ 5615	



a) Binning Structure (IF = 1080 mA, Tc = 25 °C)

CRI (R _a) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)
							42	4340 ~ 4720
		SPHWW1HDNE25YHU24J	ΥH	U2	UB	4J	43	4720 ~ 5100
		3FHWWIHDNE23TH0243	ГП	02	UB	40	44	5100 ~ 5480
							45	5480 ~ 5860
							42	4340 ~ 4720
	3500	SPHWW1HDNE25YHU34J	ΥH	U3	UA, UB	4J	43	4720 ~ 5100
	5500	SF11WW111D14231110340		00	0A, 0D	40	44	5100 ~ 5480
							45	5480 ~ 5860
		SPHWW1HDNE25YHU24G	ΥH	U2	UB	4G	44	5100 ~ 5480
		SPHWWINDNE25TH024G	тп	02	UB	40	45	5480 ~ 5860
			VII	110		40	44	5100 ~ 5480
		SPHWW1HDNE25YHU34G	ΥH	U3	UA, UB	4G	45	5480 ~ 5860
							42	4465 ~ 4855
			VII	то	тр	4.1	43	4855 ~ 5245
		SPHWW1HDNE25YHT24J	ΥH	T2	ТВ	4J	44	5245 ~ 5635
							45	5635 ~ 6025
							42	4465 ~ 4855
	1000			70			43	4855 ~ 5245
	4000	SPHWW1HDNE25YHT34J	ΥH	Т3	ΤΑ, ΤΒ	4J	44	5245 ~ 5635
							45	5635 ~ 6025
	T						44	5245 ~ 5635
80		SPHWW1HDNE25YHT24G	ΥH	T2	ТВ	4G	45	5635 ~ 6025
	Ĩ	T	T	SPHWW1HDNF25YHT34G VH T3		_	44	5245 ~ 5635
		SPHWW1HDNE25YHT34G	ΥH	Т3	TA, TB	4G	45	5635 ~ 6025
							42	4505 ~ 4900
							43	4900 ~ 5295
		SPHCW1HDNE25YHR34J	ΥH	R3	RA	4J	44	5295 ~ 5690
							45	5690 ~ 6085
							42	4505 ~ 4900
					RW, RX		43	4900 ~ 5295
	5000	SPHCW1HDNE25YHRT4J	YH	RT	RY, RZ	4J	44	5295 ~ 5690
							45	5690 ~ 6085
							44	5295 ~ 5690
		SPHCW1HDNE25YHR34G	ΥH	R3	RA	4G	45	5690 ~ 6085
					RW, RX		44	5295 ~ 5690
		SPHCW1HDNE25YHRT4G	ΥH	RT	RY, RZ	4G	45	5690 ~ 6085
							42	4505 ~ 4900
					QW, QX		43	4900 ~ 5295
		SPHCW1HDNE25YHQT4J	ΥH	QT	QV, QX QY, QZ	4J	44	5295 ~ 5690
	5700						45	5690 ~ 6085
							44	5295 ~ 5690
		SPHCW1HDNE25YHQT4G	ΥH	QT	QW, QX QY, QZ	4G	45	5690 ~ 6085



a) Binning Structure (IF = 1080 mA, Tc = 25 °C)

CRI (R₂) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)
							42	3465 ~ 3795
		SPHWW1HDNE27YHW24J	ΥH	W2	WB	4J	43	3795 ~ 4126
	2700						44	4126 ~ 4456
	2100						42	3465 ~ 3795
		SPHWW1HDNE27YHW34J	ΥH	W3	WA,WB	4J	43	3795 ~ 4126
							44	4126 ~ 4456
							42	3536 ~ 3873
		SPHWW1HDNE27YHV24J	ΥH	V2	VB	4J	43	3873 ~ 4210
	3000						44	4210 ~ 4546
							42	3536 ~ 3873
		SPHWW1HDNE27YHV34J	ΥH	V3	VA,VB	4J	43	3873 ~ 4210
90							44	4210 ~ 4546
			N/L				42	3642 ~ 3989
		SPHWW1HDNE27YHU24J	ΥH	U2	UB	4J	43	3989 ~ 4336
	3500						44	4336 ~ 4683
							42	3642 ~ 3989
		SPHWW1HDNE27YHU34J	ΥH	U3	UA,UB	4J	43	3989 ~ 4336
							44	4336 ~ 4683
							42	3748 ~ 4105
	4000	SPHWW1HDNE27YHT24J	ΥH	T2	ТВ	4J	43	4105 ~ 4462
							44	4462 ~ 4819
							42	3748 ~ 4105
		SPHWW1HDNE27YHT34J	ΥH	Т3	TA,TB	4J	43	4105 ~ 4462
							44	4462 ~ 4819

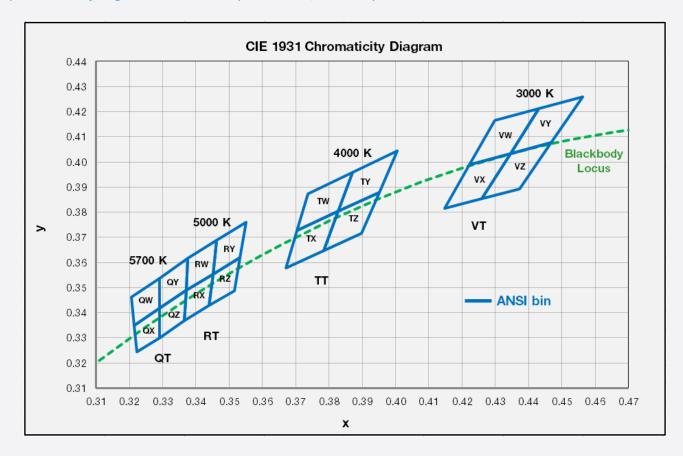


a) Binning Structure (I_F = 1080 mA, T_c = 25 °C)

CRI (R₂) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)
		SPHWW1HDNE28YHW23M	ΥH	W2	WB	3M -	31	3394 ~ 3771
	2700	SPRWWINDINE20TRW23W	тп	VVZ	VVD	3171	32	3771 ~ 4148
	2700	SPHWW1HDNE28YHW33M	ΥH	W3	WA,WB	3M -	31	3394 ~ 3771
		SPRWWINDINE20TRW33W	тп	003	VVA,VVD	3171	32	3771 ~ 4148
		SPHWW1HDNE28YHV23M	ΥH	V2	VB	3M -	31	3499 ~ 3888
95	2000	5PHVVVIHDINE201HV23IVI	тп	٧Z	VD	3171	32	3888 ~ 4276
90	3000	SPHWW1HDNE28YHV33M	YH	V3		014	31	3499 ~ 3888
		SPHWWIHDINE20THV33M	тн	Vð	VA,VB	3M -	32	3888 ~ 4276
				110		014	31	3604 ~ 4004
	2500	SPHWW1HDNE28YHU23M	ΥH	U2	UB	3M -	32	4004 ~ 4405
	3500			110		014	31	3604 ~ 4004
		SPHWW1HDNE28YHU33M	YH	U3	UA,UB	3M -	32	4004 ~ 4405





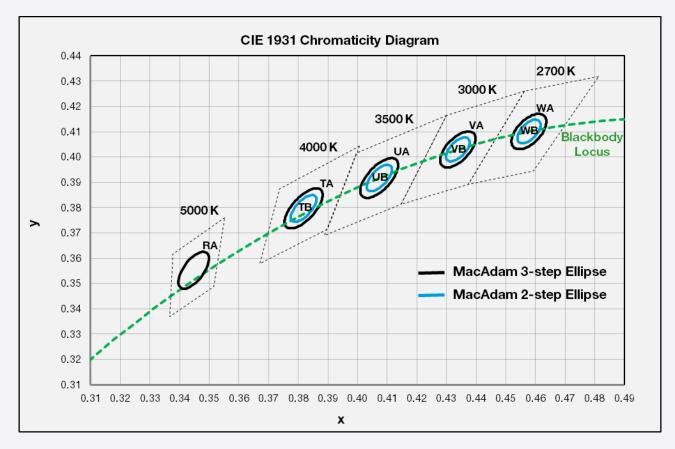


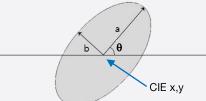
Region	CIE x	CIE y	Region	CIE x	CIE y
		V rank	(3000 K)		
	0.4223	0.399		0.4345	0.4033
VW	0.4345	0.4033	VY	0.4468	0.4077
VVV	0.4431	0.4213	VY	0.4562	0.4260
	0.4299	0.4165		0.4431	0.4213
	0.4223	0.399		0.4260	0.3854
VX	0.4147	0.3814	1/7	0.4373	0.3893
VX	0.4260	0.3854	VZ	0.4468	0.4077
	0.4345	0.4033		0.4345	0.4033
		R rank	(5000 K)		
	0.3376	0.3616		0.3463	0.3687
DW	0.3463	0.3687	DV(0.3551	0.3760
RW	0.3451	0.3554	RY	0.3533	0.3620
	0.3371	0.3490		0.3451	0.3554
	0.3371	0.3490		0.3451	0.3554
DY	0.3451	0.3554	67	0.3533	0.3620
RX	0.3440	0.3428	RZ	0.3515	0.3487
	0.3366	0.3369		0.3440	0.3428

Region	CIE x	CIE y	Region	CIE x	CIE y		
	T rank (4000 K)						
	0.3736	0.3874		0.3871	0.3959		
714/	0.3871	0.3959		0.4006	0.4044		
I VV	TW 0.3828 0.3803 TY	0.3952	0.388				
	0.3703	0.3726		0.3828	0.3803		
	0.3703	0.3726		0.3828	0.3803		
ТХ	0.3828	0.3803	77	0.3952	0.388		
IX	0.3784	0.3647	TZ	0.3898	0.3716		
	0.367	0.3578		0.3784	0.3647		
		Q rank	(5700 K)				
	0.3207	0.3462		0.3290	0.3538		
011/	0.3290	0.3538		0.3376	0.3616		
QW	0.3290	0.3417	QY	0.3371	0.3490		
	0.3215	0.3350		0.3290	0.3417		
	0.3215	0.3350		0.3290	0.3417		
OY	0.3290	0.3417	07	0.3371	0.3490		
QX	0.3290	0.3300	QZ	0.3366	0.3369		
	0.3222	0.3243		0.3290	0.3300		









	MacAdam Ellipse (WA, WB)							
Step CIE x CIE y θ a b								
2-step	0.4578	0.4101	53.70	0.0054	0.0028			
3-step	0.4578	0.4101	53.70	0.0081	0.0042			

MacAdam Ellipse (UA, UB)							
Step CIE x CIE y θ a b							
2-step	0.4073	0.3917	54.00	0.0062	0.0028		
3-step	0.4073	0.3917	54.00	0.0093	0.0041		

	MacAdam Ellipse (RA)						
Step CIE x CIE y θ						b	
	3-step	0.3447	0.3553	59.62	0.0082	0.0035	

Ν	ote:	

Samsung maintains measurement tolerance of: Cx, $Cy = \pm 0.005$

MacAdam Ellipse (VA, VB)						
Step CIE x CIE y θ a b						
2-step	0.4338	0.403	53.22	0.0056	0.0027	
3-step	0.4338	0.4030	53.22	0.0083	0.0041	

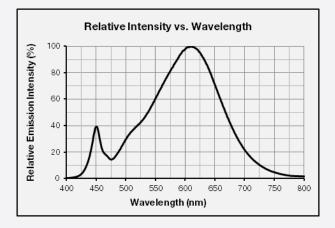
	MacAdam Ellipse (TA, TB)						
Step	Step CIE x CIE y θ a b						
2-step	0.3818	0.3797	53.72	0.0063	0.0027		
3-step	0.3818	0.3797	53.72	0.0094	0.0040		



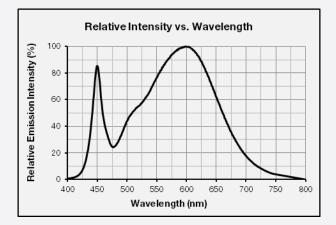
3. Typical Characteristics Graphs

a) Spectrum Distribution ($I_F = 1080 \text{ mA}, T_c = 25 \text{ °C}$)

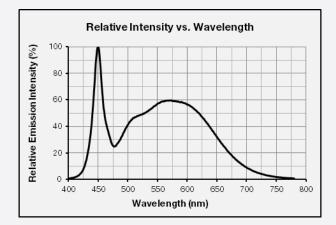
CCT: 2700 K (80 CRI)



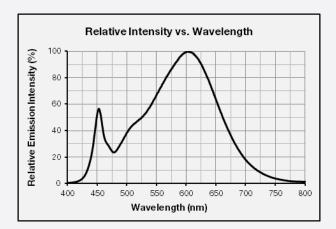
CCT: 3500 K (80 CRI)



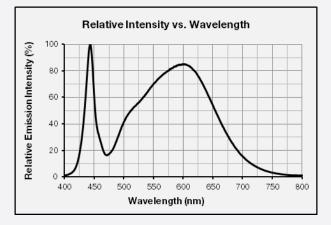
CCT: 5000 K (80 CRI)



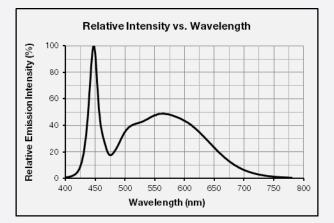
CCT: 3000 K (80 CRI)



CCT: 4000 K (80 CRI)

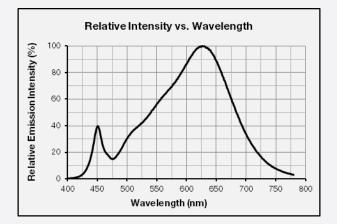


CCT: 5700 K (80 CRI)

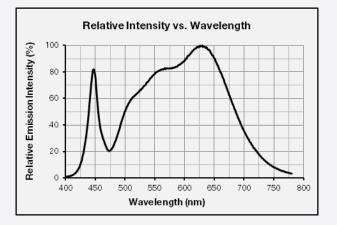




CCT: 2700 K (90 CRI)

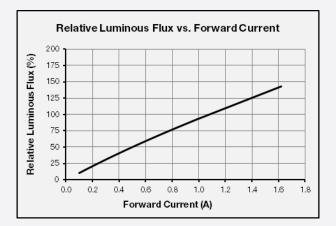


CCT: 3500 K (90 CRI)

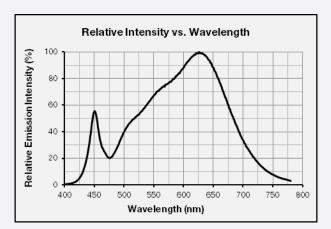


b) Forward Current Characteristics (T_c = 25 °C)

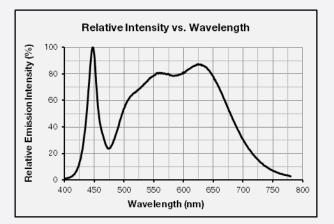
80 CRI

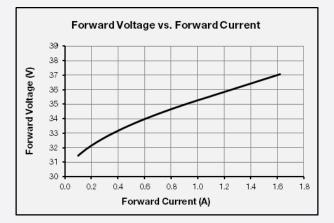






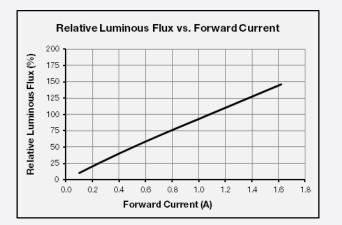
CCT: 4000 K (90 CRI)

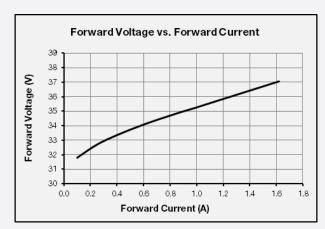






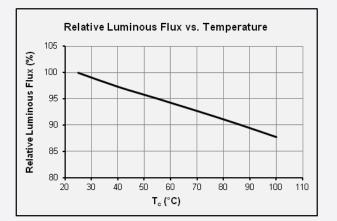




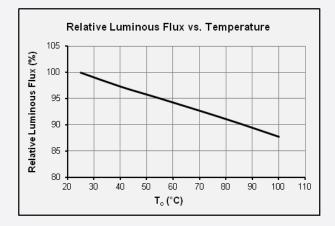


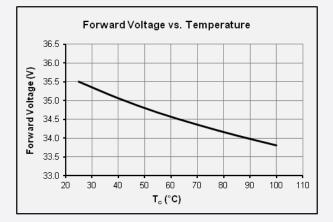
c) Temperature Characteristics (I_F = 1080 mA)

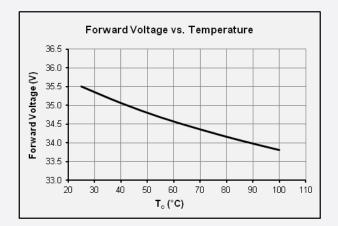
80 CRI



90 CRI





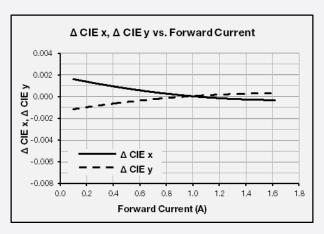




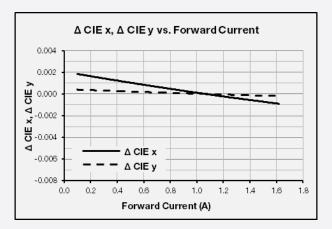
d) Color Shift Characteristics

T_c = 25 °C

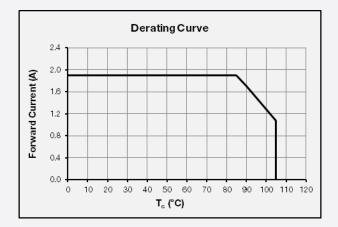
80 CRI

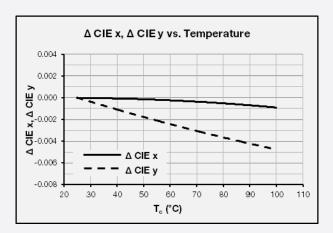


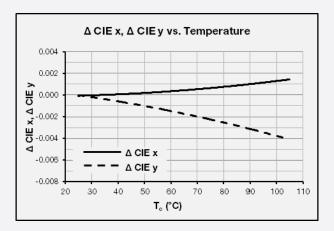




e) Derating Curve

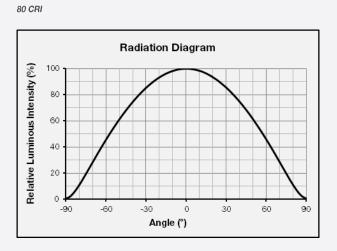




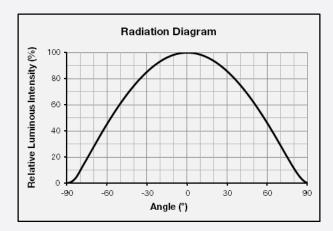




f) Beam Angle Characteristics (IF = 1080 mA, T_{\circ} = 25 °C)

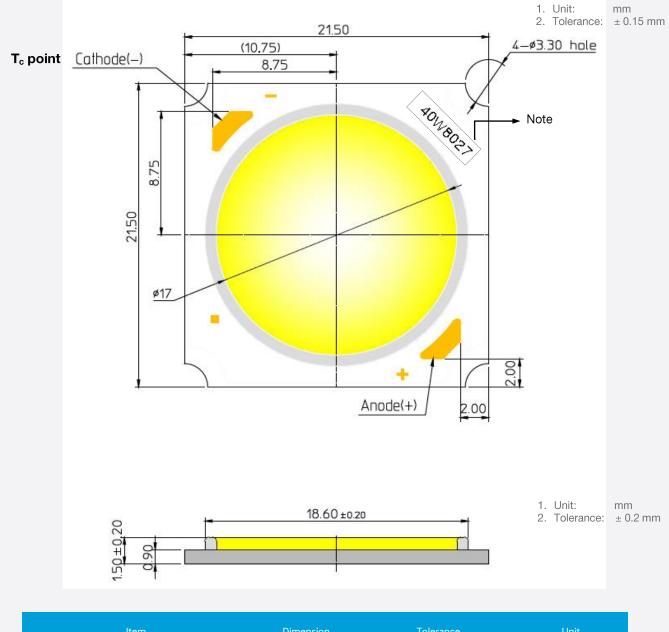


90 CRI



SAMSUNG

4. Outline Drawing & Dimension



Item	Dimension	Tolerance	Unit
Length	21.50	±0.15	mm
Width	21.50	±0.15	mm
Height	1.50	±0.20	mm
Light Emitting Surface (LES) Diameter	17	±0.15	mm

Note: Denoted product information above is only an example (40W8027:40W, CRI80+, 2700K)



5. Reliability Test Items & Conditions

a) Test Items

Test Item	Test Condition	Test Hour / Cycle
Room Temperature Life Test	25 °C, I _F = max	1000 h
High Temperature Humidity Life Test	85 °C, 85 % RH, DC Derating, I _F = max	1000 h
High Temperature Life Test	105 °C, DC Derating, $I_F = max$	1000 h
Low Temperature Life Test	-40 °C, DC 1900 mA	1000 h
High Temperature Storage	120 °C	1000 h
Low Temperature Storage	-40 °C	1000 h
Thermal Shock	-45 °C / 15 min ↔ 125 °C / 15 min temperature change in 5 min	200 cycles
Temperature Cycle On/Off Test	-40 °C / 85 °C each 20 min, 100 min transfer power on/off each 5 min, DC 1080 mA	100 cycles
Temperature Humidity Storage Test	-10 °C ↔ 25 °C, 95 % RH ↔ 85 °C, 95 % RH (24 h / cycle)	100 cycles
ESD (HBM)	R1: 10 MΩ R2: 1.5 kΩ C: 100 pF V: ±2 kV	5 times
ESD (MM)	R ₁ : 10 MΩ R ₂ : 0 kΩ C: 200 pF V: ±0.5 kV	5 times
Vibration Test	20 ~ 80 Hz (displacement: 0.06 inch, max. 20 g) 80 ~ 2 kHz (max. 20 g) min. frequency ↔ max. frequency 4 min transfer	4 times
Mechanical Shock Test	1500 g, 0.5 ms each of the 6 surfaces (3 axis x 2 sides)	5 times
Salt Spray Test	35 °C, 5 % salt water 8 h spray, 16 h dwell	2 cycles

b) Criteria for Judging the Damage

Item	Symbol	Test Condition	Limit		
Item	Symbol	(T _c = 25 °C)	Min.	Max.	
Forward Voltage	VF	I _F = 1080 mA	L.S.L. * 0.9	U.S.L. * 1.1	
Luminous Flux	Φ_{v}	$I_{\rm F} = 1080 \mbox{ mA}$	L.S.L * 0.7	U.S.L * 1.3	



6. Label Structure

a) Label Structure

Aluminum Bag & Inner Box **Outer Box** 300000 YHRW42 <u>YHRW42</u> Rank SPHCW1HDNE25YHRT4J YHRW42 01 SPHCW1HDNE25YHRT4J YHRW42 01 Code Lot number OEB1906001/60 OEB1906011/60 OEB1906001/60 OEB1906002/60 OEB1906002/60 OEB1906012/60 Tray OEB1906003/60 OEB1906003/60 OEB1906013/60 number OEB1906004/60 /Q'ty OEB1906004/60 OEB1906005/60 OEB1906005/60 OEB1906006/60 OEB1906007/60 OEB1906008/60 OEB1906009/60 OEB1906010/60 SAMSUNG SAMSUNG [Box Label]

Note: Denoted rank code and product code above is only an example (see description on page 6)

Rank Code:

- (a)(b): Forward Voltage rank (refer to page 7-10)
- © d: Chromaticity bin (refer to page 11-12)
- (e)(f): Luminous Flux bin (refer to page 7-10)



b) Lot Number

The lot number is composed of the following characters:

$\bigcirc \bigcirc \diamondsuit \blacklozenge \square \blacksquare \triangle \triangle \triangle / 1 \blacktriangle \blacktriangle \triangle / xxx PCS$

•	: Production site (S: Giheung, Korea, G: Tianjin, China)
\odot	: L (LED)
\diamond	: Product state (A: Normal, B: Bulk, C: First Production, R: Reproduction, S: Sample)
•	: Year (Y: 2014, Z: 2015, A: 2016,)
	: Month (1~9, A, B, C)
	: Day (1~9, A, B~V)
$\triangle \triangle \triangle$: Product serial number (001 ~ 009)
	: Tray number (001 ~ 999)

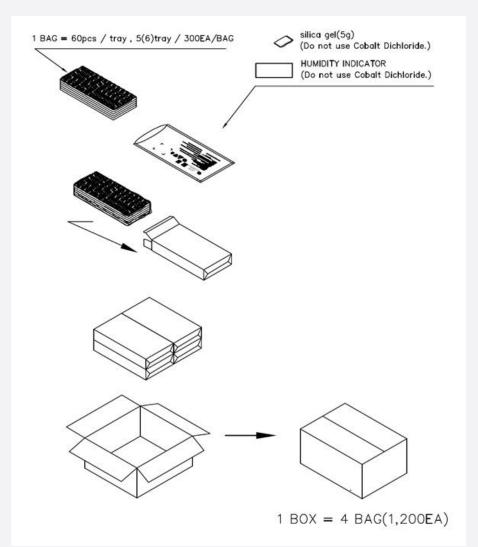
21



7. Packing Structure

Packing material	Max. quantity	Dimension (mm)			
Packing material	in pcs of COB	Length	Width	Height	Tolerance
Tray	60	322.6	135.9	11	0.25
Aluminum Bag	300 (5 trays)	450	230	-	10
PE Foam Pad	-	280	130	10	2
Inner Box	300 (1 aluminum bag)	338	148	55	2
Outer Box	1200 (4 inner boxes)	351	308	120	5
Pallet	67,200 (56 outer boxes)	1000	1000	970	10

a) Packing Structure for 5 trays inside Aluminum Bag

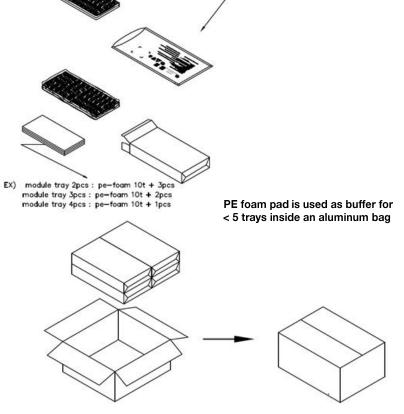




b) Packing Structure for < 5 trays inside Aluminum Bag

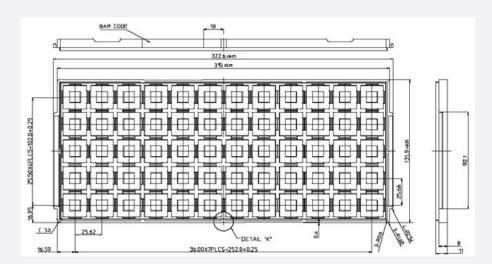
1 BAG = 60pcs / tray





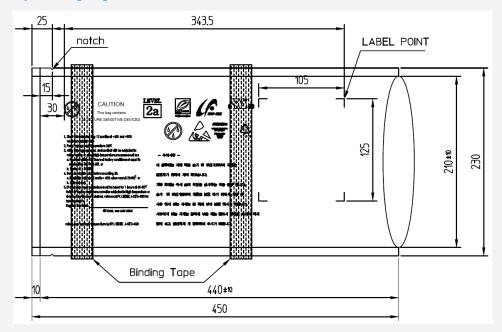
0

c) Tray





d) Aluminum Vinyl Packing Bag



e) Silica Gel & Humidity Indicator Card inside Aluminum Vinyl Packing Bag





8. Precautions in Handling & Use

- This device should not be used in any type of fluid such as water, oil, organic solvent, etc. When cleaning is required, IPA is recommended as the cleaning agent. Some solvent-based cleaning agent may damage the silicone resins used in the device.
- 2) LEDs must be stored in a clean environment. If the LEDs are to be stored for three months or more after being shipped from Samsung, they should be packed with a nitrogen-filled container (shelf life of sealed bags is 12 months at temperature 0~40 °C, 0~90 % RH).
- After storage bag is opened, device subjected to soldering, solder reflow, or other high temperature processes must be:
 a. Mounted within 672 hours (28 days) at an assembly line with a condition of no more than 30 °C / 60 % RH, or
 b. Stored at <10 % RH
- 4) Repack unused products with anti-moisture packing, fold to close any opening and then store in a dry place.
- 5) Devices require baking before mounting, if humidity card reading is >60 % at 23 ± 5 °C.
- 6) Devices must be baked for 1 hour at 60 \pm 5 °C, if baking is required.
- 7) The LEDs are sensitive to the static electricity and surge current. It is recommended to use a wrist band or anti-electrostatic glove when handling the LEDs. If voltage exceeding the absolute maximum rating is applied to LEDs, it may cause damage or even destruction to LED devices. Damaged LEDs may show some unusual characteristics such as increase in leakage current, lowered turn-on voltage, or abnormal lighting of LEDs at low current.
- 8) VOCs (Volatile Organic Compounds) can be generated from adhesives, flux, hardener or organic additives used in luminaires (fixtures). Transparent LED silicone encapsulant is permeable to those chemicals and they may lead to a discoloration of encapsulant when they exposed to heat or light. This phenomenon can cause a significant loss of light emitted (output) from the luminaires. In order to prevent these problems, we recommend users to know the physical properties of materials used in luminaires and they must be carefully selected.
- 9) The resin area is very sensitive, please do not handle, press, touch, rub, clean, or pick by with tweezers on it. Instead, please pick at the handling area as indicated below.

